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Application No. 09/129,113

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Docket No.: 50349CPA2(70329)

AMENDMENTS TO THE CLAIMS

1-42. (cancelled)

43. (previously presented) A positive-acting photoresist composition comprising:

- 1) a component that comprises photoacid-labile groups;
- 2) a triphenyl sulfonium salt photoacid generator compound having a cation component that is substituted with one or more of a moiety that has at least 4 carbon atoms and is selected from optionally substituted alkyl, optionally substituted alkenyl, optionally substituted alkynyl, optionally substituted heteroalkyl, optionally substituted heteroalkenyl or optionally substituted heteroalkynyl,

and the photoacid generator compound having an anion compound that is i) an arylsulfonate counter anion substituted with one or more electron-withdrawing groups or ii) an alicyclic moiety that is substituted with one or more electron-withdrawing groups.;
and

- 3) propylene glycol methyl ether acetate, and wherein the composition contains less than about 10 weight percent, based on total weight of the composition, of a hydrolytic solvent.

44. (cancelled)

45. (previously presented) The photoresist of claim 43 wherein the photoacid generator is a triphenyl sulfonium salt that has one or more phenyl groups substituted by the moieties.

46. (previously presented) The photoresist of claim 43 wherein the photoacid generator is substituted with a moiety having 5 or more carbon atoms.

47. (previously presented) The photoresist of claim 43 wherein the photoacid generator is substituted with a moiety having 6 or more carbon atoms.

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48. (previously presented) The photoresist of claim 43 wherein the photoacid generator is substituted by one or more alkoxy groups.

49. (previously presented) The photoresist of claim 43 wherein the photoacid generator is substituted by one or more alkyl groups.

50. (cancelled)

51. (previously presented) The photoresist of claim 50 wherein the photoresist composition contains less than about 2 weight percent of a hydroxylic solvent, based on total weight of the composition.

52. (currently amended) A method for forming a photoresist relief image onto a substrate comprising:

- a) applying a coating layer of a photoresist composition of claim 43 on a substrate; and
- b) exposing and developing the photoresist coating layer to provide a photoresist relief image of the photoresist composition.

53. (previously presented) An article of manufacture comprising a substrate having coated thereon the photoresist of claim 1.

54. (previously presented) The article of claim 53 wherein the substrate is a microelectronic wafer.

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